

## CLAIMS

What is claimed is:

1.           A method comprising:  
  
              providing a coating over a wafer, wherein the coating comprises at least one  
  
              characteristic of a single crystal;  
  
              testing a semiconductor tool using the wafer; and  
  
              refreshing the coating of the wafer.
2.           The method of Claim 1, wherein the testing comprises:  
  
              providing a film over the surface of the wafer; and  
  
              testing at least one characteristic of the film.
3.           The method of Claim 2, wherein the at least one characteristic of the film  
comprises uniformity of thickness of the film.
4.           The method of Claim 2, wherein the at least one characteristic of the film  
comprises grain size.
5.           The method of Claim 2, wherein the at least one characteristic of the film  
comprises ability to polish the wafer.

6. The method of Claim 1, further comprising testing surface contaminant adding properties of the semiconductor tool.
7. The method of Claim 6, wherein the testing surface contaminant adding properties comprises testing light scattering properties of a surface of the wafer.
8. The method of Claim 1, wherein the single crystal characteristic comprises insignificant distortion of an angle of refraction of incident light.
9. A method comprising:
- providing a coating over a wafer, wherein the coating comprises at least one characteristic of a single crystal;
  - removing surface contaminants from the wafer; and
  - refreshing the coating of the wafer.
10. The method of Claim 9, wherein the providing the coating comprises:
- providing a polysilicon layer; and
  - surface polishing the polysilicon layer.

11. The method of Claim 9, wherein the removing surface contaminants comprises:  
  
utilizing a chemical cleaning procedure.
12. The method of Claim 9, wherein the refreshing the coating of the wafer comprises:  
  
mechanically grinding the coating;  
  
providing a polysilicon layer; and  
  
surface polishing the polysilicon layer.
13. The method of Claim 9, wherein the single crystal characteristic comprises insignificant distortion of an angle of refraction of incident light.
14. An apparatus comprising:  
  
a semiconductor tool testing configuration;  
  
a test wafer comprising a silicon wafer including coating refreshed at least twice.
15. The apparatus of Claim 14, wherein the semiconductor tool testing configuration determines light scattering properties of a surface of the wafer.

16. The apparatus of Claim 14, wherein the semiconductor tool testing configuration comprises:

a film provider to provide a film layer over the test wafer; and

a film property measurer to determine film properties.

17. The apparatus of Claim 16, wherein the film property measurer determines an extent of light scattering defects on a surface of the film.

18. The apparatus of Claim 16, wherein the film property measurer determines particles and light scattering defects.

19. The apparatus of Claim 16, wherein the film property measurer determines uniformity of thickness of the film.

20. The apparatus of Claim 16, wherein the film property measurer determines grain size of the film.

21. The apparatus of Claim 16, wherein the film property measurer determines ability to polish the wafer.